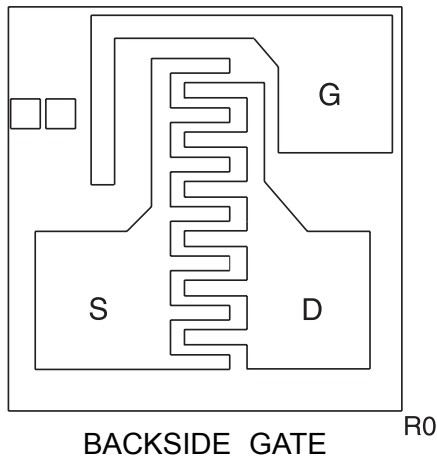


PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	15 x 15 MILS
Die Thickness	8.0 MILS
Drain Bonding Pad Area	3.2 X 4.0 MILS
Source Bonding Pad Area	3.2 X 4.0 MILS
Gate Bonding Pad Area	3.2 X 4.0 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 6,000Å

GEOMETRY

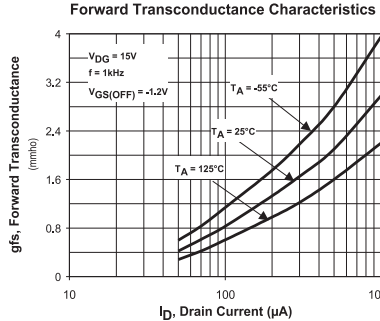
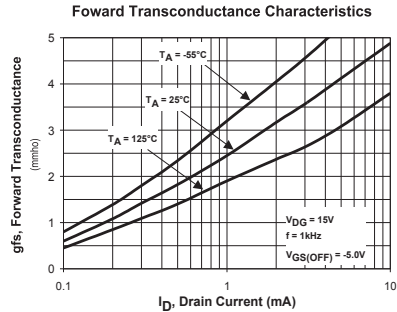
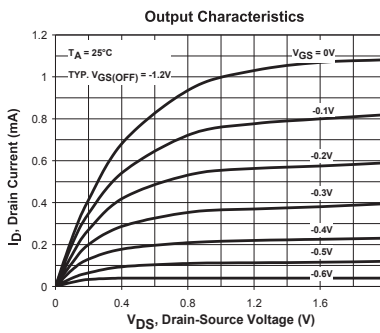
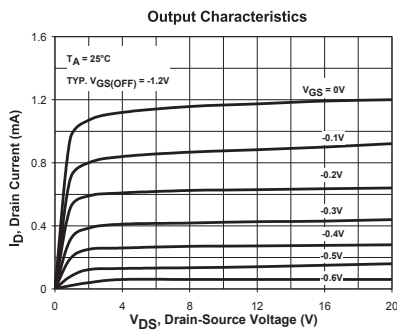
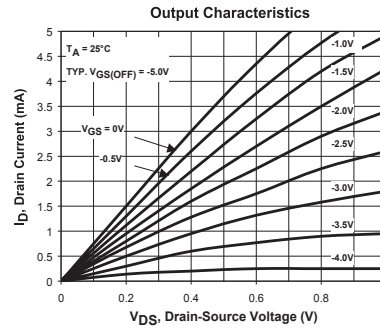
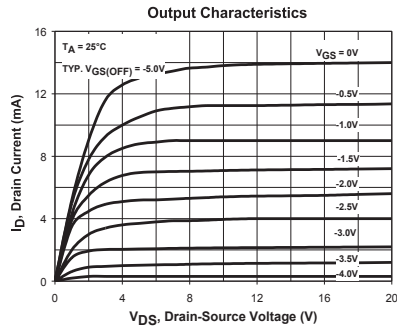


GROSS DIE PER 4 INCH WAFER
53,730

PRINCIPAL DEVICE TYPES
2N4416A
CMPF4416A

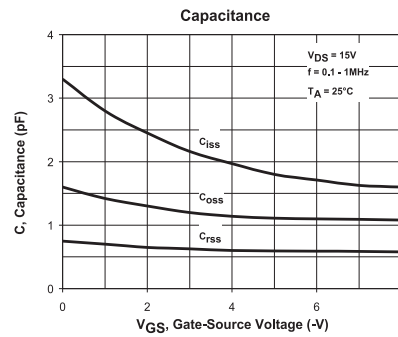
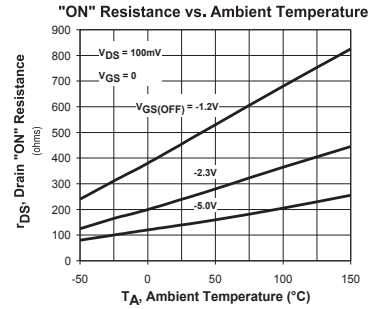
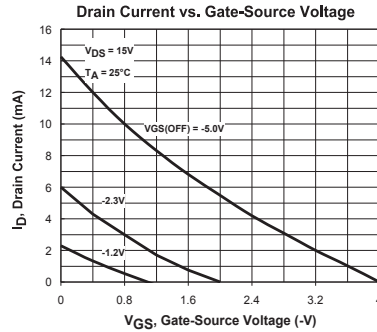
145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centrasemi.com

R3 (9 -September 2003)



145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centralsemi.com

R3 (9 -September 2003)



145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centalsemi.com

R3 (9 -September 2003)